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APPLICATION NO. FILING DATE		G DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/604,514 07/28/2003		28/2003	Masuhiro Natsuhara	39.020-AG	1513	
29453	7590	06/06/2006		EXAMINER		
	MURAKAN BUILDING, 7	/II IP ASSOCIA?	KACKAR, RAM N			
	•	HOME, KITA-KU	ART UNIT	PAPER NUMBER		
OSAKA-SI	HI, 530-004	<b>1</b> 7	1763 DATE MAILED: 06/06/2006			
JAPAN						

Please find below and/or attached an Office communication concerning this application or proceeding.

•		Applicat	ion No.	Applicant(s)				
Office Action Summary		10/604,5	514	NATSUHARA ET AL.				
		Examine	er	Art Unit				
		Ram N. I		1763				
 Period for	The MAILING DATE of this communication Reply	appears on th	e cover sheet with the c	orrespondence ad	Idress			
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).								
Status								
1)⊠ F	Responsive to communication(s) filed on <u>02 April 2006</u> .							
2a) <u></u> ⊤	This action is <b>FINAL</b> . 2b) This action is non-final.							
3)□ S	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits							
C	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.							
Dispositio	n of Claims							
4; 5)□ 0 6)⊠ 0 7)□ 0	Claim(s) 1-10 is/are pending in the application.  4a) Of the above claim(s) is/are withdrawn from consideration.  Claim(s) is/are allowed.  Claim(s) 1-10 is/are rejected.  Claim(s) is/are objected to.  Claim(s) is/are objected to.							
Applicatio	n Papers							
<ul> <li>9) The specification is objected to by the Examiner.</li> <li>10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.  Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).</li> <li>11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.</li> </ul>								
Priority un	der 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) All b) Some * c) None of:  1. Certified copies of the priority documents have been received.  2. Certified copies of the priority documents have been received in Application No  3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  * See the attached detailed Office action for a list of the certified copies not received.								
2) 🔲 Notice ( 3) 🔲 Informa	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948) tion Disclosure Statement(s) (PTO-1449 or PTO/SB No(s)/Mail Date		4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal Pa 6) Other:	te	D-152)			

### **DETAILED ACTION**

# Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 4/2/2006 has been entered.

# Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1, 2, 4, 6-7 and 9 are rejected under 35 U.S.C. 102(b) as being anticipated by Harada et al (WO 0154188).

Harada et al disclose an electrostatic chuck with porous metallic sprayed electrode of tungsten with a porosity of 1-7% (See Col 3 lines 26-46, Col 6 lines 15-25 and Col 10 lines 40-47 in US 6771483- an English equivalent).

Application/Control Number: 10/604,514 Page 3

Art Unit: 1763

## Claim Rejections - 35 USC § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

5. Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shamouilian et al (US 6494958) in view of Heimann et al (US 6620707).

Shamouilian et al disclose a wafer holder for a semiconductor manufacturing equipment (Fig 1-210) having a surface for carrying wafers and an electrical circuitry (electrode) formed inside (Fig 1-220 or 230), the electrical circuitry having porosity (large range of mesh size of 5-200 - Col 9 lines 42-46) and comprising silver, molybdenum, tantalum, tungsten or platinum (Col 9 lines 33-38). The electrode could be an RF electrode (Col 5 lines 48-50) or an electrostatic chuck (Col 4 lines 35-37). The wafer holder including the electrode could be made by sintering (Col 7 lines 9-14).

Shamouilian et al teach that due to voids or interstices between the wires (pores) the mesh is subject to less thermal expansion. It is therefore obvious that adjustment of mesh size could allow adjustment of thermal expansion and the integrity of the wafer holder through large number of cycles of expansion and contraction.

Regarding the limitation of porosity being 0.1% -40% the mesh size could control the porosity of the electrode to any percentage needed.

Sintered electrode of platinum for heating is disclosed by Heimann et al (Col 1 lines 48-57) who teach that electrodes are usually manufactured by sintering (Col 1 lines 30-32) and disclose the pros and cons of low porosity vs high porosity and recommends suitable sintering temperature for porosity required.

It is held that it is obvious to optimize Result-Effective Variables MPEP 2144.05 II B In re Antonie, 559 F.2d 618, 195 USPQ 6 (CCPA 1977) See also In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980). It is clear from the teaching of Heimann et al that the porosity is a result effective parameter.

Therefore it would have been obvious for one of ordinary skill in the art at the time of invention to make the electrode as sintered as an alternative and art recognized equivalent to porous mesh and have a porosity of 0.1-40%.

6. Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Niori et al (US 6197246) in view of Heimann et al (US 6620707).

Niori et al disclose a wafer holder for a semiconductor manufacturing equipment (Fig 7-41) having a surface for carrying wafers and an electrical circuitry (electrode) formed inside (30), the electrical circuitry having porosity (mesh size) and comprising molybdenum, tantalum, tungsten or platinum (Col 10 lines 57 to Col 11-line8). The electrode could be an RF electrode (Fig 7). Niori et al further teach that the electrode of wire mesh or plate like with numerous holes (porous) the thermal stress is dispersed (Col 10 lines 65-67).

Regarding the porosity the mesh size could control the porosity to a required degree.

Application/Control Number: 10/604,514

Art Unit: 1763

As discussed above, Heimann et al (Col 1 lines 48-57) teach that electrodes are usually manufactured by sintering (Col 1 lines 30-32) and disclose the pros and cons of low porosity vs. high porosity and recommends suitable sintering temperature for porosity required.

Therefore it would have been obvious for one of ordinary skill in the art at the time of invention to make the electrode as sintered as an alternative and art recognized equivalent to porous mesh according to the teachings of Niori et al and Heimann et al.

### Response to Arguments

Applicant's arguments filed 4/2/2006 have been fully considered but they are not persuasive.

Applicant continues to argue that Shamouilian et al do not disclose a three dimensional structure. As discussed earlier (Col 9 line 45-46), the cross-sectional shape of a circle ellipse or rectangle with a length dimension makes it a three dimensional body.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ram N. Kackar whose telephone number is 571 272 1436. The examiner can normally be reached on M-F 8:00 A.M to 5:P.M.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Parviz Hassanzadeh can be reached on 571 272 1435. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Application/Control Number: 10/604,514

Art Unit: 1763

Page 6

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

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like assistance from a USPTO Customer Service Representative or access to the automated

information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Ram Kackar

Primary Examiner AU 1763